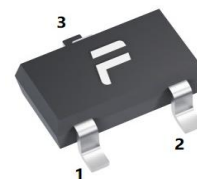
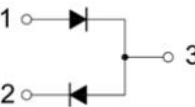
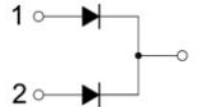
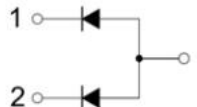


SOT-23 Schottky Barrier Diode 肖特基势垒二极管



Internal Configuration & Device Marking 内部结构与产品打标

Type 型号	BAS20-04	BAS20-05	BAS20-06
Pin 管脚			
Mark 打标	24	25	26

Absolute Maximum Ratings 最大额定值

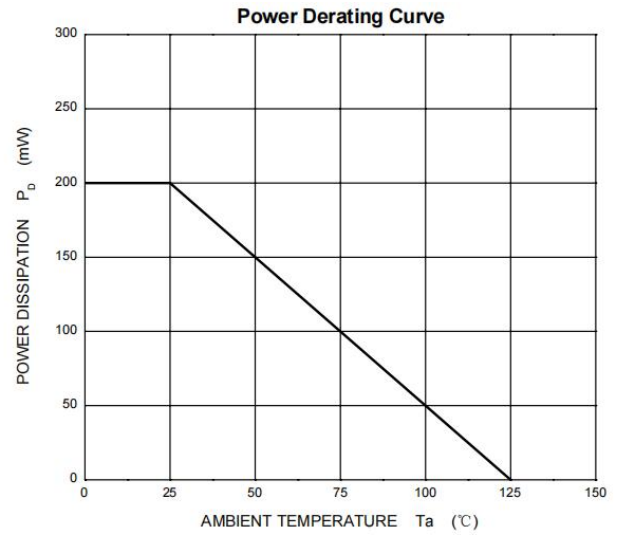
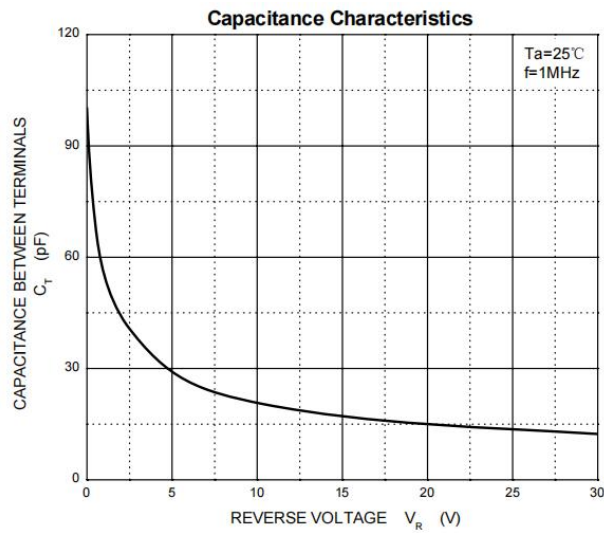
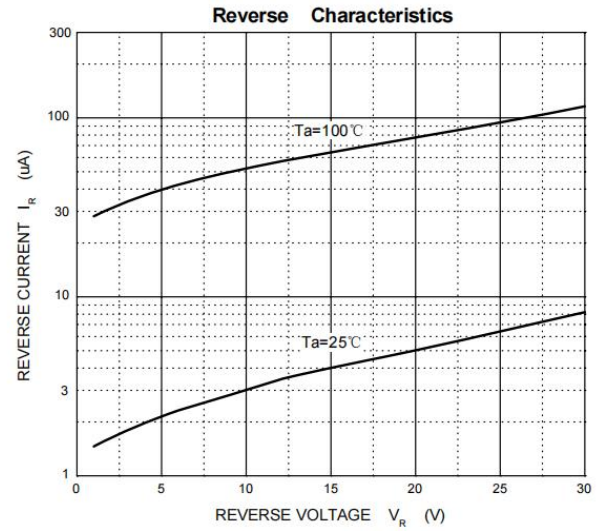
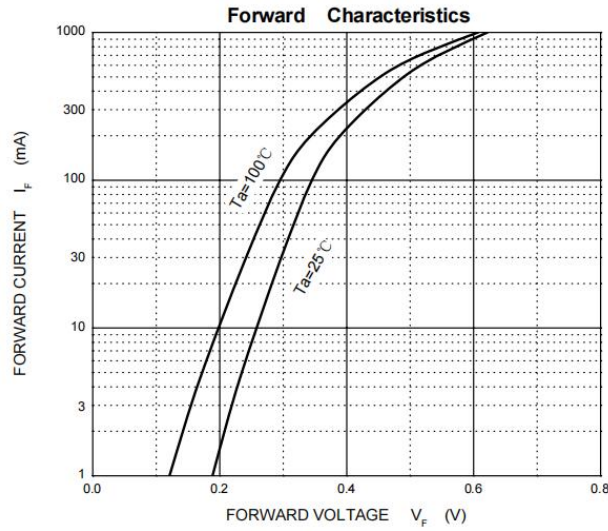
Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	20	V
Reverse Work Voltage 反向工作电压	V_{RWM}		
DC Reverse Voltage 直流反向电压	V_R		
Forward Work Current 正向工作电流	$I_F(I_O)$	500	mA
Peak Forward Current 正向峰值电流	I_{FM}	1500	mA
Non-repetitive Peak Forward Surge Current 正向峰值浪涌电流	I_{FSM}	5000	mA
Power dissipation 耗散功率	$P_D(T_a=25^{\circ}C)$	200	mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	625	$^{\circ}C/W$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	125 $^{\circ}C$, -55to+150 $^{\circ}C$	

Electrical Characteristics 电特性

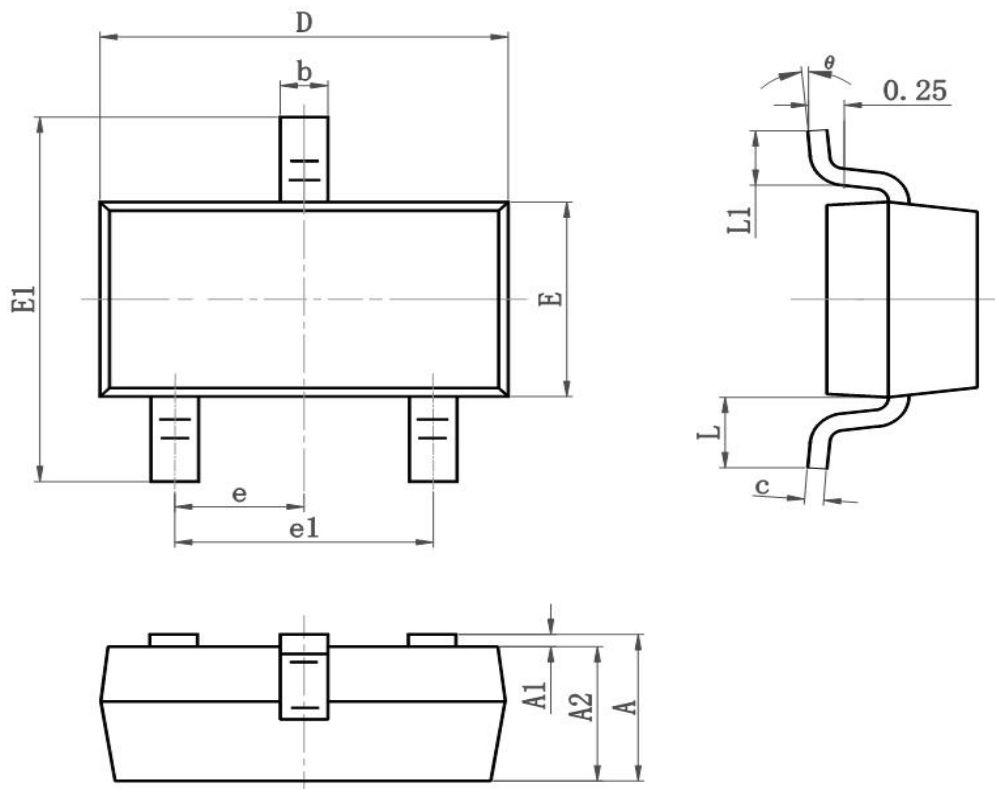
($T_A=25^{\circ}C$ unless otherwise noted 如无特殊说明, 温度为 25 $^{\circ}C$)

Characteristic 特性参数	Symbol 符号	Min 最小值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压($I_R=100\mu A$)	$V_{(BR)}$	20	—	V
Reverse Leakage Current($V_R=10V$) 反向漏电流($V_R=20V$)	I_R	—	20 100	μA
Forward Voltage($I_F=10mA$) 正向电压($I_F=100mA$) ($I_F=500mA$)	V_F	—	0.35 0.43 0.55	V
Diode Capacitance 二极管电容($V_R=0V$, $f=1MHz$)	C_T	—	120	pF
Reverse Recovery Time 反向恢复时间 $I_F=I_R=50mA$, $V_R=6V$	T_{rr}	—	20	nS

■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.050	0.055
E1	2.250	2.550	0.089	0.100
e	0.900	1.00	0.035	0.039
e1	1.800	2.000	0.071	0.079
L	0.500	0.600	0.020	0.024
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°